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Supplementary Information for

High-breakdown-voltage β-Ga_2O_3 nanoFET with a beveled field-plate structure

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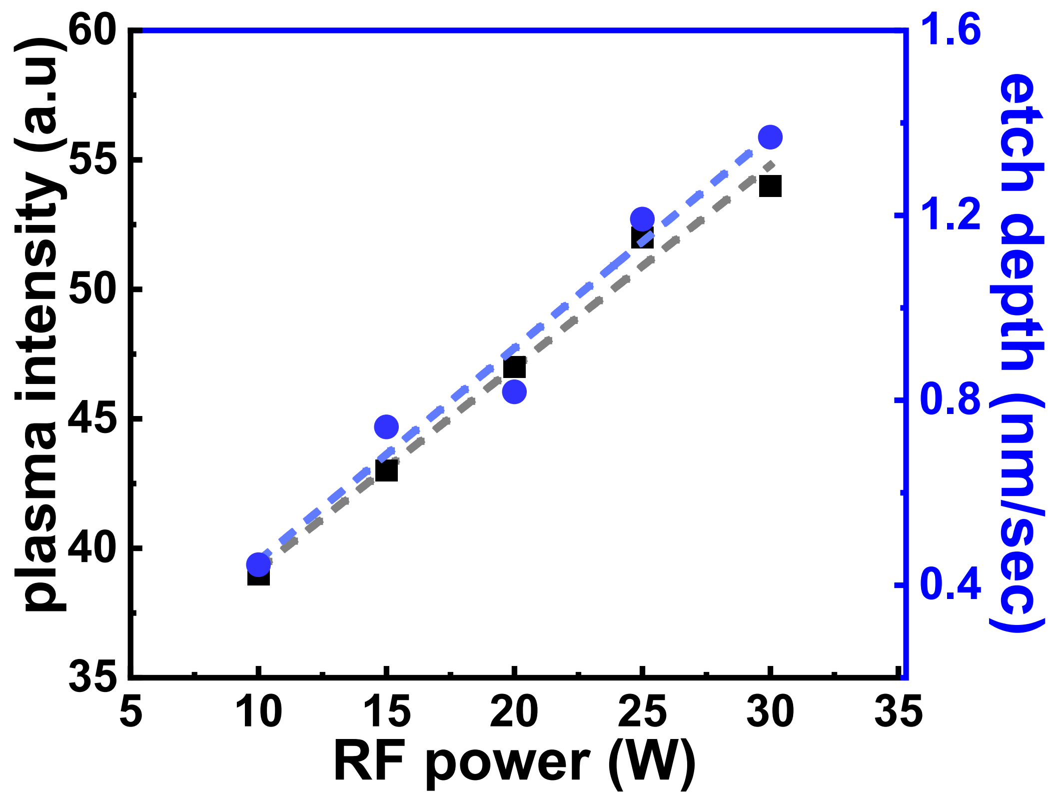

Fig. S1. Relationship between RF power and plasma intensity, and RF power and etch depth for h-BN etching.

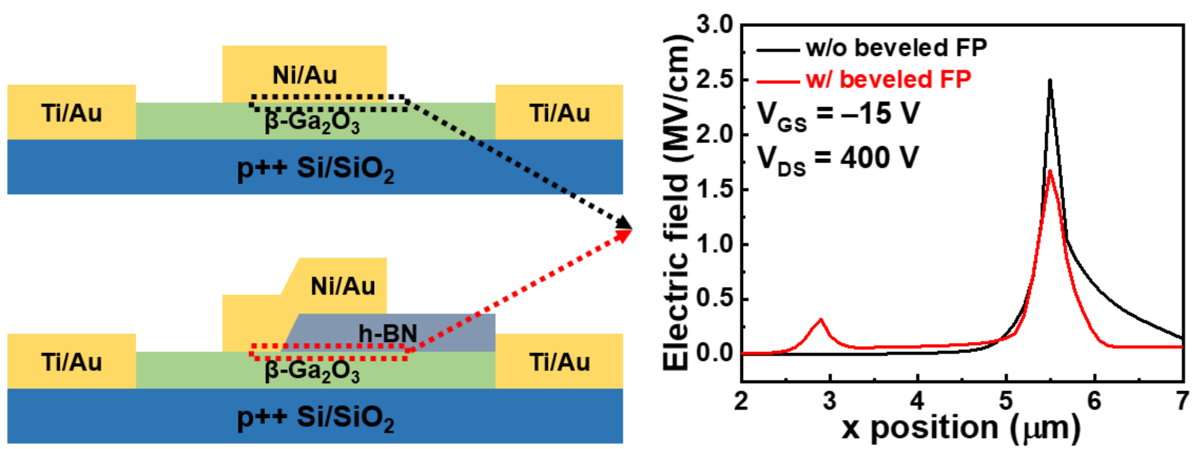

Fig. S2. The simulation of electric fields distribution on the surface of the β-Ga_2O_3 channel at V_{GS} = −15 V, V_{DS} = 400 V.

The beveled h-BN field-plate redistributes the electric fields on the surface of the β-Ga_2O_3. Fig. S2 presents the electric-field distributions calculated around the gate edge with and without the beveled field plate.